Please add the following new Abstract:

In one implementation, an etching process includes forming a carbon containing material over a substrate and plasma etching at a temperature of at least 400°C using a hydrogen or oxygen containing plasma. In one implementation, a plasma etching process includes forming openings in a masking layer over a substrate and etching material beneath the masking through the openings. The masking layer is removed and the substrate is plasma etched at a temperature of at least 400°C. In one implementation, an etching process includes forming a residue over the substrate during a first etching and subsequently plasma etching to remove the residue. In one implementation, a chemical vapor deposition process includes positioning a semiconductor substrate within a plasma enhanced chemical vapor deposition reactor, plasma etching using a first gas chemistry, depositing a material over the substrate within the reactor using a second gas chemistry.